ABSTRACT OF THE DISCLOSURE

Described is a manufacturing method of an integrated circuit which uses a thin film such as platinum or BST as a hard mask upon patterning ruthenium or the like, thereby making it possible to form a device without removing the hard mask.

In addition, the invention method makes it possible to interpose a protecting film such as platinum in order to prevent, upon removing a resist used for the patterning of the hard mask, an underlying ruthenium film or the like from being damaged.

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